

FORM PTO-1449	Atty. Docket No.: 801.12-0988/STL 11281.00	Appl. No.: Filed Herewith
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	First Named Inventor:	
	Ge Yi et al.	
	Filing Date	Group Art:
	Filed Herewith	3729

## U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
<i>MD</i>	AA	4,764,478	8/16/88	Hiruta	437	29
	AB	5,192,618	3/9/93	Frankel et al.	428	457
	AC	5,406,434	4/11/95	Amin et al.	360	126
	AD	5,936,402	8/10/99	Schep et al.	324	252
	AE	6,054,023	4/25/00	Chang et al.	204	192.2
	AF	6,383,574	5/7/02	Han et al.	427	526
	AG	6,411,478	6/25/02	Mao et al.	360	324.2
	AH	6,501,143	12/31/02	Sato et al.	257	421
	AI	6,515,341	2/4/03	Engel et al.	257	421
<i>MD</i>	AJ	US2002/009 4374	7/18/02	Han et al.	427	128
	AK					

## FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub Class	Translation Yes No
<i>MD</i>	AL	WO 02/095434 A1	11/28/02	WO	—	X (abstract only)
	AM					
	AN					

EXAMINER:

DATE CONSIDERED:

2/28/06

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>1101</u>	AO	H.D. Chopra and S.Z. Hua, "Ballistic Magnetoresistance over 3000% in Ni nanicontacts at room temperature," Phys. Rev. B66 (2002) 020403R
		G. Prinz, "Magnetoelectronics," Science 282 (1998) 1660
		S.H. Chung et al., "Universal Scaling of Ballistic Magnetoresistance in Magnetic nanocontacts," Phy. Rev. Lett. 89 (2002) 287203
		P. Bruno, "Geometrically Constrained Magnetic Wall," Phys. Rev. Lett. 83 (1999) 2425
		N. Garcia et al., "Magnetoresistance in excess of 200% in Ballistic Ni Nanocontacts at Room Temperature and 100 Oe," Phys. Rev. Lett. 82 (1999) 2923
		G. Tatara et al., "Domain Wall Scattering Explains 300% Ballistic Magnetoconductance of Nanocontacts," Phys. Rev. Lett. 83 (1999) 2030
		M. Munoz et al., "Ballistic magnetoresistance in a nanocontact between a Ni cluster and a magnetic thin film," Appl. Phys. Lett. 79 (2001) 2946
		Kaminsky et al., "Patterning ferromagnetism in Ni <sub>80</sub> Fe <sub>20</sub> films using Ga <sup>+</sup> ion irradiation," Appl. Phys. Lett. 78 (2001) 1589
		C. Chappert et al., "Planar Patterned Magnetic media obtained by ion irradiation," Science, 280 (1998) 1919
		Fadei Komarov ed., "Ion beam Modification of Metals," OPA (Amsterdam) 1992, p. 130
		Phil Schewe et al., "Ballistic Magnetoresistance," Physics News Update (2002) 1 page
		"Ballistic Magnetoresistance," Physics News Graphics, (2002), 3 pages
	AP	R. Colin Johnson, "Nanocontacts could make hard drives go 'ballistic,' The Work Circuit, 4 pages (May 27, 2003)
<u>1101</u>	AQ	Roger D. Pease et al., "The Future of Memory and Storage Technology," ELEC 694 (2002)

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